Claims

1. Bipolar transistor, comprising
an emitter area which can be contacted electrically via an emitter electrode;
a base area which can be contacted electrically via a base electrode;
a collector area which can be contacted electrically via a collector electrode;
wherein at least one electrode of the emitter, base and collector electrodes is a polysilicon layer, into which doping is inserted, and wherein into the at least one electrode, in addition to the doping, impurity atoms with a density of $10^{19}$ - $10^{21}$ $cm^{-3}$ are inserted, the impurity atoms being C, P or Ar atoms.

2. Bipolar transistor according to Claim 1,
wherein the polysilicon layer is doped with boron atoms.

3. Bipolar transistor according to Claim 2,
wherein the concentration of the boron atoms is chosen to be greater than 5 x $10^{20}$ $cm^{-3}$.

4. Bipolar transistor according to Claim 1,
wherein the at least one electrode consists of polycrystalline silicon-germanium.

5. Bipolar transistor according to Claim 1,
wherein the at least one electrode is the base electrode.

6. Bipolar transistor according to Claim 1,
wherein the bipolar transistor is a self-aligned bipolar transistor.